

ポスター発表（12月3日 17時30分～）

タイトル(和/英)

著者(和/英)

所属(和/英)

ポスター順

P-1 Nonlocal spin transport in a Kondo Alloy Cu(Fe)

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P-2 Perpendicular anisotropy and damping constant of single and double CoFeB-MgO interface structures with various CoFeB thicknesses

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P-3 Voltage-controlled magnetic anisotropy for CoFe ultrathin films

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P-4 The electric field control of perpendicular magnetic anisotropy in Pt/Co system with Pd layer insertion

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P-5 Voltage noise induced by phase transition in chiral magnets

Yuhki Shimada, and Jun-ichiro Ohe

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P-6 Band structure near the Fermi level in the ferromagnetic semiconductor GaMnAs studied by ultrafast time-resolved light-induced reflectivity measurements

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P-7 (Ga,Mn)As:Liの面内異方性磁気抵抗効果の温度依存性

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P-8 Separation of the valence band and impurity band associated with the ferromagnetic transition in GaMnAs

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P-9 Anomalous Temperature Dependence of Magnetization in Ferromagnetic Mn-doped ZnSnAs₂ Thin Films

S. Hidaka, H. Toyota and N. Uchitomi

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P-10 Fabrication of CdTe self-assembled dots containing a single Cr atom and single-dot spectroscopy

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P-11 Fabrication and Electrical Conductivity Measurement of SmO Epitaxial Thin Film

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P-12 Solid phase epitaxial growth of layered Y₂O₂Bi thin film with Bi²⁻ square net

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P-13 CoFe/TiO₂/Siトンネルコンタクトを用いたSiへのスピン注入

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1東工大像情報, 2東工大電子物理

P-14 Dynamical spin injection and transport in n-type 4H-SiC

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P-15 Design of electric-field-assisted nonlocal silicon-channel spin devices

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P-16 Room-temperature spin injection into n-Ge by using Co₂FeSi_{0.5}Al_{0.5}/n⁺-Ge electrodes

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P-17 Growth condition dependence of carrier and spin lifetimes in GaAs/AlGaAs quantum wells at room temperature

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P-18 Magneto-transport properties in layered semiconductor GaSe thin films

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